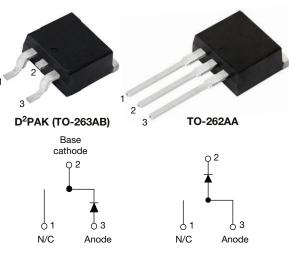
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# VS-MURB820-M3, VS-MURB820-1-M3

**Vishay Semiconductors** 

# Ultrafast Rectifier, 8 A FRED Pt<sup>®</sup>



VS-MURB820-M3

VS-MURB820-1-M3

PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	8 A			
V <sub>R</sub>	200 V			
V <sub>F</sub> at I <sub>F</sub>	0.895 V			
t <sub>rr</sub>	35 ns			
T <sub>J</sub> max.	175 °C			
Package	D <sup>2</sup> PAK (TO-263AB), TO-262AA			
Circuit configuration	Single			

### **FEATURES**

- Ultrafast recovery time
- · Low forward voltage drop
- Low leakage current
- 175 °C operating junction temperature
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- · Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

### **DESCRIPTION / APPLICATIONS**

MUR.. series are the state of the art ultrafast recovery rectifiers specifically designed with optimized performance of forward voltage drop and ultrafast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS	i			
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Peak repetitive reverse voltage	V <sub>RRM</sub>		200	V
Average rectified forward current	I <sub>F(AV)</sub>	Total device, rated V <sub>R</sub> , T <sub>C</sub> = 150 °C	8	
Non-repetitive peak surge current	I <sub>FSM</sub>		100	А
Peak repetitive forward current	I <sub>FM</sub>	Rated V <sub>R</sub> , square wave, 20 kHz, T <sub>C</sub> = 150 °C	16	
Operating junction and storage temperatures	TJ, T <sub>Stg</sub>		-65 to +175	°C

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)								
PARAMETER	ARAMETER SYMBOL TEST CONDITIONS					UNITS		
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	I <sub>R</sub> = 100 μA	200	-	-			
	VF	I <sub>F</sub> = 8 A	-	-	0.975	V		
Forward voltage	VF	I <sub>F</sub> = 8 A, T <sub>J</sub> = 150 °C	-	-	0.895	0.895		
		$V_{R} = V_{R}$ rated	-	-	5			
Reverse leakage current	IR	$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	V µA pF		
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	25	-	pF		
Series inductance	LS	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

Revision: 25-Oct-17

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RoHS

COMPLIANT

HALOGEN

FREE



# VS-MURB820-M3, VS-MURB820-1-M3

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### **Vishay Semiconductors**

DYNAMIC RECOVERY	CHARAC	TERISTICS ( $T_J$ :	= 25 °C unless oth	nerwise sp	ecified)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	50 A/µs, V <sub>R</sub> = 30 V	-	-	35	
Reverse recovery time	+	I <sub>F</sub> = 0.5 A, I <sub>R</sub> = 1.0	A, I <sub>REC</sub> = 0.25 A	-	-	25	ns
Reverse recovery time	t <sub>rr</sub>	T <sub>J</sub> = 25 °C		-	20	-	
		T <sub>J</sub> = 125 °C		-	34	-	
Pools receivers ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C	$I_F = 8 A$	-	1.7	-	А
Peak recovery current		T <sub>J</sub> = 125 °C	dl <sub>F</sub> /dt = 200 A/µs V <sub>B</sub> = 160 V	-	4.2	-	
	0	T <sub>J</sub> = 25 °C	VH - 100 V	-	23	-	nC
Reverse recovery charge	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	75	-	

THERMAL - MECHAN		CIFICATIONS				
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		-65	-	175	°C
Thermal resistance, junction-to-case	R <sub>thJC</sub>		-	-	3.0	
Thermal resistance, junction-to-ambient	R <sub>thJA</sub>		-	-	50	°C/W
Thermal resistance, case-to-heatsink	R <sub>thCS</sub>	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
weight			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking daviaa		Case style D <sup>2</sup> PAK (TO-263AB)		MUR	B820	•
Marking device		Case style TO-262AA		MURE	3820-1	

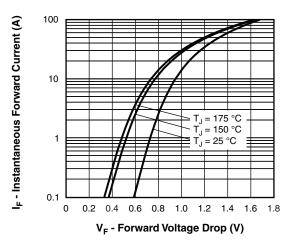


Fig. 1 - Typical Forward Voltage Drop Characteristics

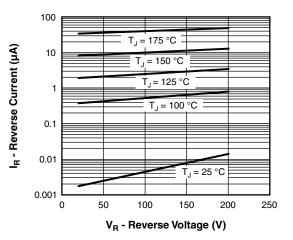


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

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## VS-MURB820-M3, VS-MURB820-1-M3

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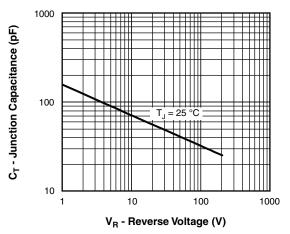


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

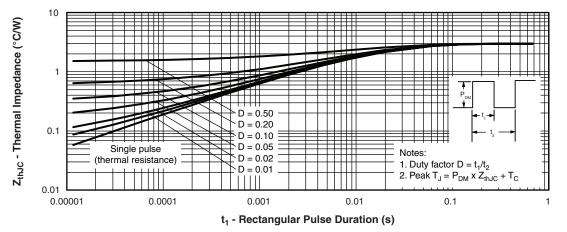
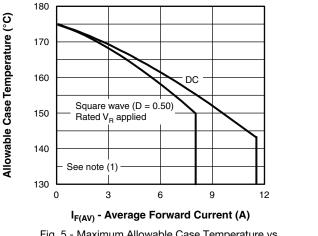
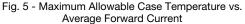
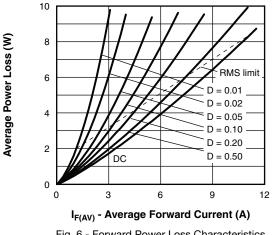


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics







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# VS-MURB820-M3, VS-MURB820-1-M3



### **Vishay Semiconductors**

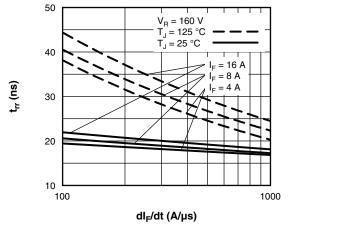
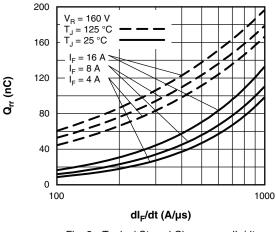
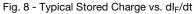


Fig. 7 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt





#### Note

<sup>(1)</sup> Formula used:  $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$ ;

Pd = forward power loss =  $I_{F(AV)} \times V_{FM}$  at  $(I_{F(AV)}/D)$  (see fig. 6); Pd<sub>REV</sub> = inverse power loss =  $V_{R1} \times I_R$  (1 - D);  $I_R$  at  $V_{R1}$  = rated  $V_R$ 

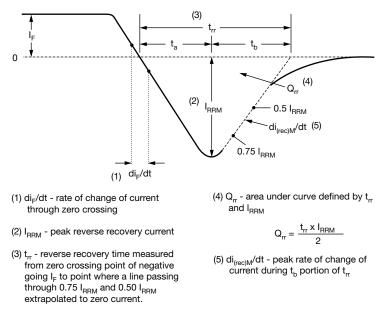
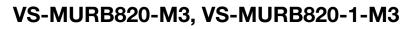


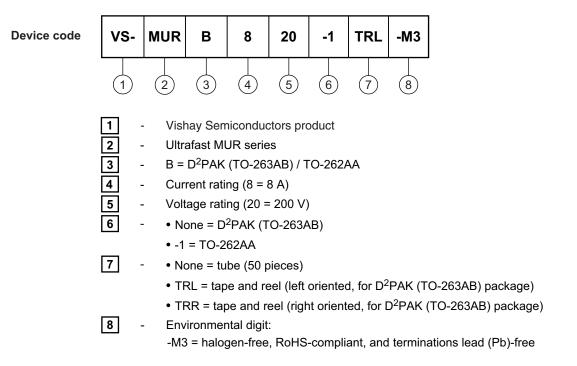
Fig. 9 - Reverse Recovery Waveform and Definitions





### **Vishay Semiconductors**

### **ORDERING INFORMATION TABLE**



	LINKS TO RELATED	DOCUMENTS
Dimensions —	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96164
Dimensions	TO-262AA	www.vishay.com/doc?96165
Port marking information	ng information D <sup>2</sup> PAK (TO-263AB) <u>www.vishay.com/doc?95444</u> TO-262AA <u>www.vishay.com/doc?95443</u>	www.vishay.com/doc?95444
		www.vishay.com/doc?95443
Packaging information	D <sup>2</sup> PAK (TO-263AB)	www.vishay.com/doc?96424

**Vishay Semiconductors** 

D<sup>2</sup>PAK

### **DIMENSIONS** in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN. MAX.		MIN.	MAX.	NOTES	
А	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

	SYMBOL	MILLIM	ETERS	INC	HES	NOTES
		MIN.	MAX.	MIN.	MAX.	NOTES
	D1	6.86	8.00	0.270	0.315	3
	E	9.65	10.67	0.380	0.420	2, 3
	E1	7.90	8.80	0.311	0.346	3
	е	2.54 BSC		0.100 BSC		
	Н	14.61	15.88	0.575	0.625	
	L	1.78	2.79	0.070	0.110	
	L1	-	1.65	-	0.066	3
	L2	1.27	1.78	0.050	0.070	
	L3	0.25	0.25 BSC		BSC	
	L4	4.78	5.28	0.188	0.208	

### Notes

<sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

<sup>(7)</sup> Outline conforms to JEDEC<sup>®</sup> outline TO-263AB

Revision: 13-Jul-17

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Document Number: 96164

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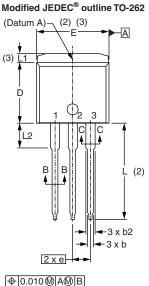
## **Outline Dimensions**

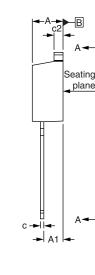


**Vishay Semiconductors** 

**TO-262AA** 

### **DIMENSIONS** in millimeters and inches





F D1 (3) (3) Section A - A Base (4) Plating b1. b3 metal ≰ c1 (4) -(b, b2)-Section B - B and C - C Scale: None





Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode

Lead assignments

CYMPOL	MILLIN	IETERS	INC	HES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54	BSC	0.100	) BSC	
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

 <sup>(1)</sup> Dimensioning and tolerancing as per ASME Y14.5M-1994
<sup>(2)</sup> Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the second dimensioner of the second dimensis and the second dimensioner of the second dimensioner of the the outmost extremes of the plastic body (3)

Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only (5)

Controlling dimension: inches

(6) Outline conform to JEDEC® TO-262 except A1 (max.), b (min., max.), b1 (min.), b2 (max.), c (min.), c1(min.), c2 (max.), D (min.), E (max.), L1 (max.), L2 (min., max.)

Revision: 30-Nov-17

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